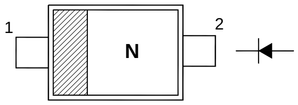
1SS373WT

Silicon Epitaxial Schottky Barrier Diode

for high speed switching application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



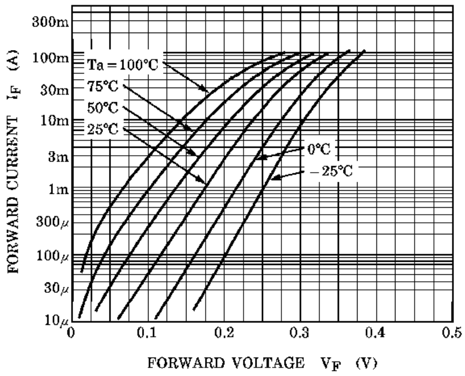
Top View
Marking Code: "**N**"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

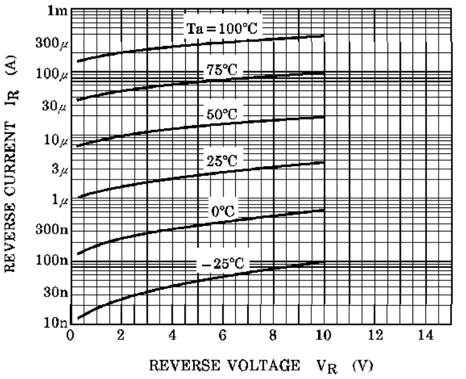
Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Average Forward Current	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current	I_{FM}	200	mA
Surge Current (10 ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	150	mW
Operating Temperature Range	T_{opr}	- 40 to + 100	°C
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

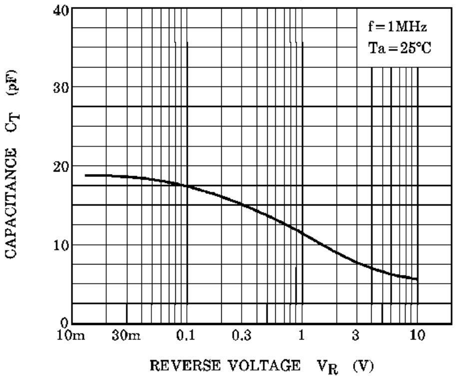
Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 5 mA at I_F = 100 mA	V_F	 0.3 0.5	V
Reverse Current at V_R = 10 V	I_R	20	µA
Total Capacitance at V_R = 0, f = 1 MHz	C_T	40	pF



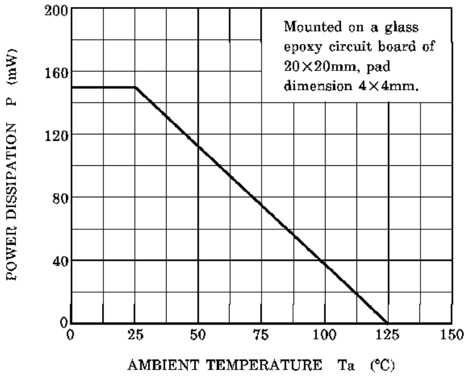
$I_F - V_F$



$I_R - V_R$



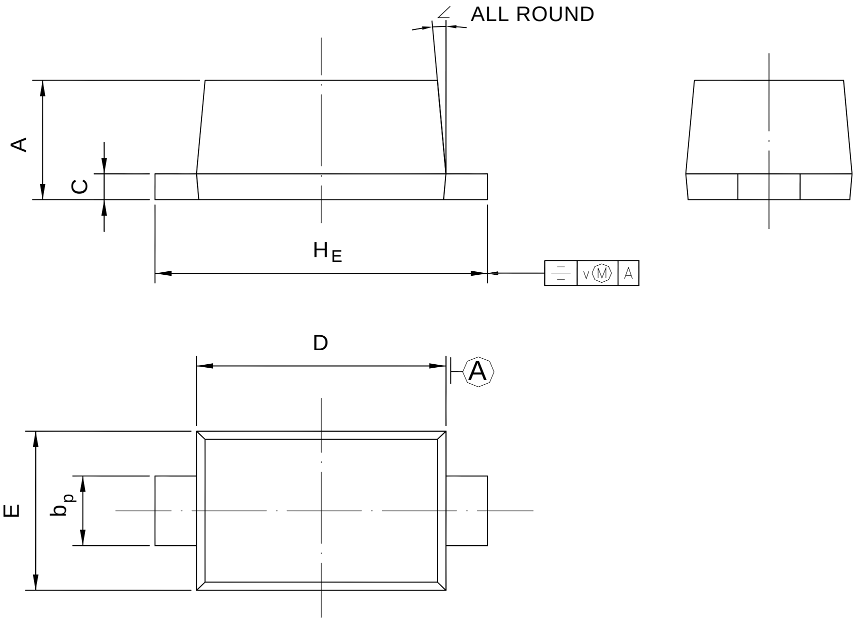
$C_T - V_R$



P − Ta

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°